

FQP7P06-VB Datasheet

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS}	-60	V
$R_{DS(on)}$ $V_{GS} = 10\text{ V}$	62	$m\Omega$
$R_{DS(on)}$ $V_{GS} = 4.5\text{ V}$	74	$m\Omega$
I_D	-40	A
Configuration	Single	

FEATURES

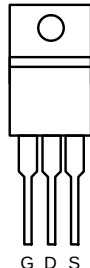
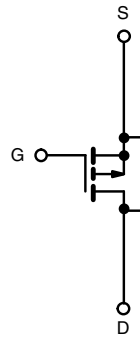
- Trench Power MOSFET
- 100 % UIS Tested

APPLICATIONS

- Load Switch


RoHS
 COMPLIANT

TO-220AB


 G D S
 Top View


P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted

Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175\text{ }^\circ\text{C}$)	$T_C = 25\text{ }^\circ\text{C}$	I_D	-40	A
	$T_C = 100\text{ }^\circ\text{C}$		-30	
Pulsed Drain Current		I_{DM}	- 90	
Continuing Source Current (Diode Conduction)		I_S	- 30	
Avalanche Current		I_{AS}	- 28	
Single Pulse Avalanche Energy	$L = 0.1\text{ mH}$	E_{AS}	7.2	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	60 ^a	W
	$T_A = 25\text{ }^\circ\text{C}$		2 ^b	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient ^b	$t \leq 10\text{ sec}$	R_{thJA}	20	25	$^\circ\text{C/W}$
	Steady State		62	75	
Junction-to-Case		R_{thJC}	5	6	

Notes:

a. See SOA curve for voltage derating.

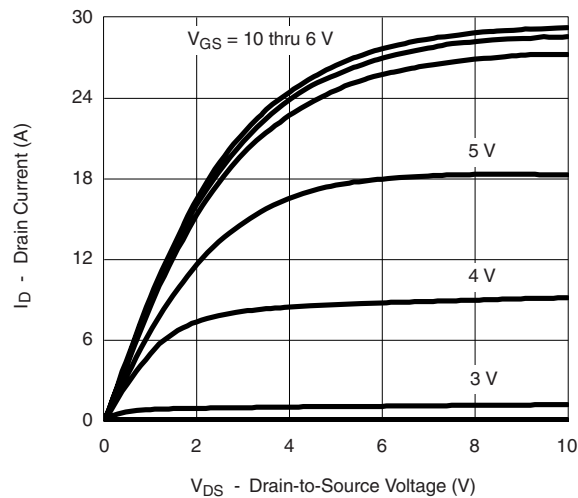
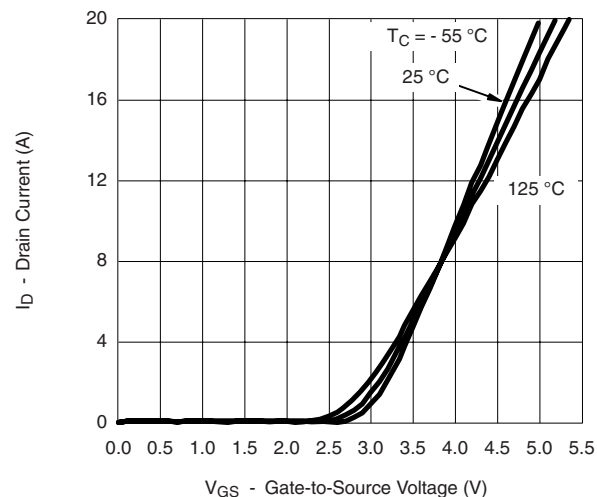
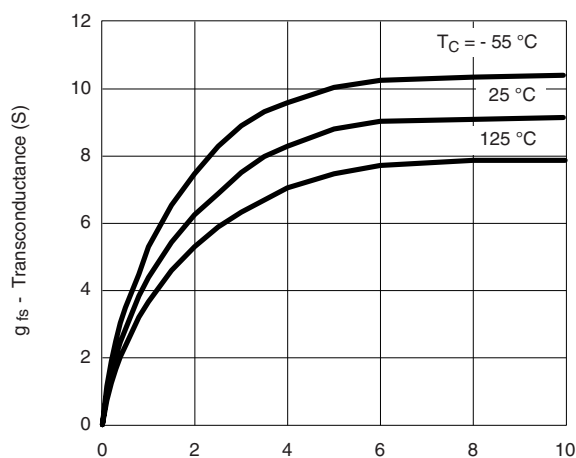
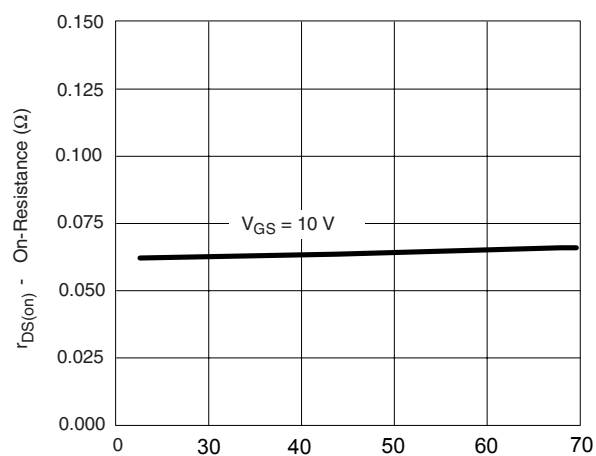
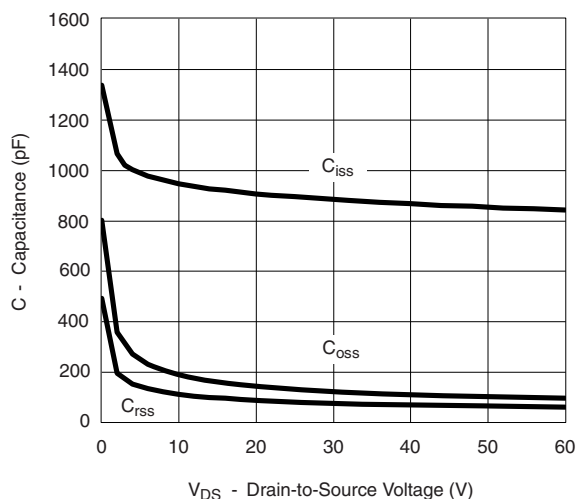
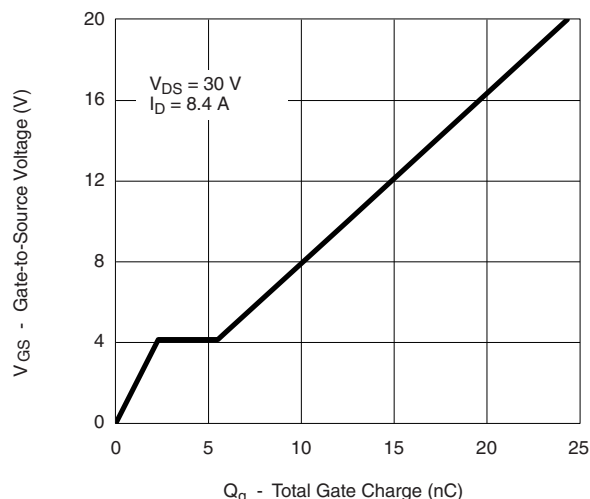
b. Surface Mounted on 1" x 1" FR-4 board.

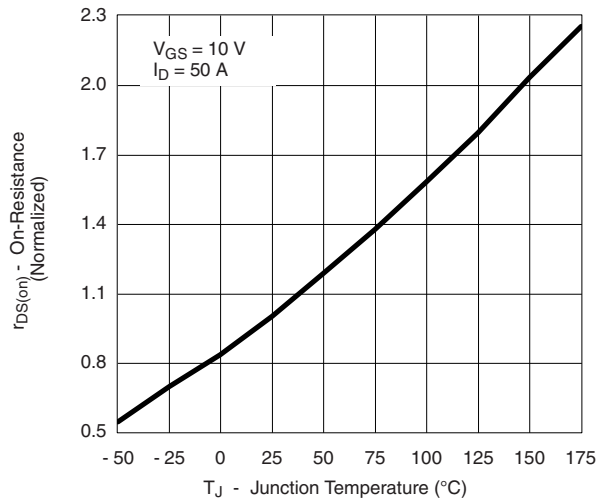
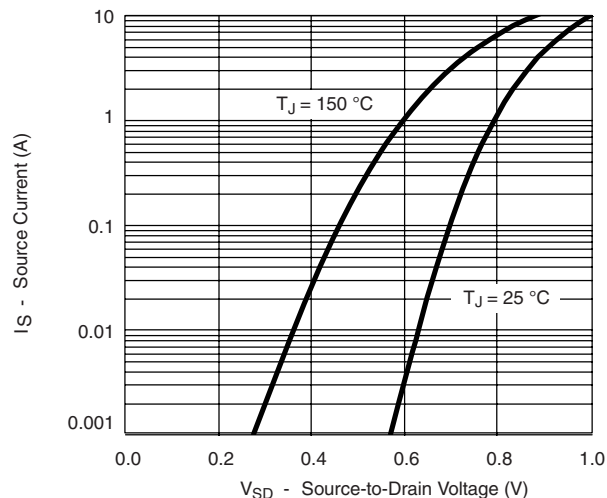
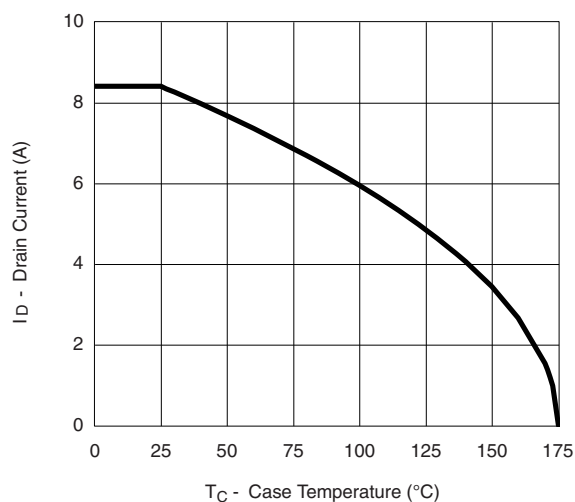
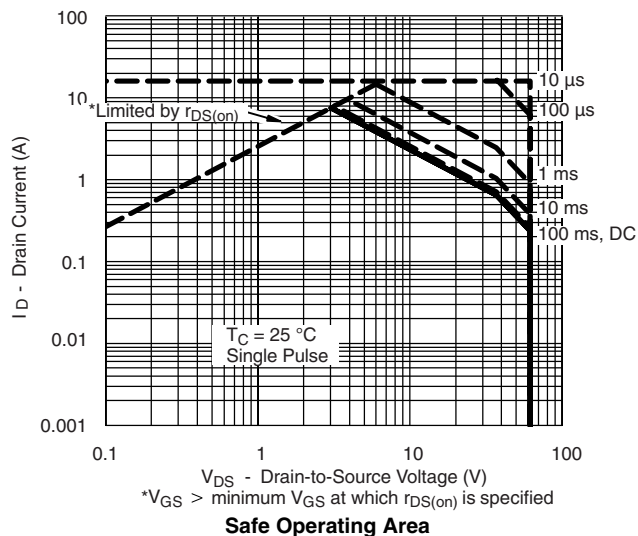
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.0		- 3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 125 °C			- 50	
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 175 °C			- 150	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 10			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = - 10 V, I _D = - 5 A		62		mΩ
		V _{GS} = - 10 V, I _D = - 5 A, T _J = 125 °C		80		
		V _{GS} = - 10 V, I _D = - 5 A, T _J = 175 °C		110		
		V _{GS} = - 4.5 V, I _D = - 2 A		74		
Forward Transconductance ^b	g _{fs}	V _{DS} = - 15 V, I _D = - 5 A		8		S
Dynamic						
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		1300		pF
Output Capacitance	C _{oss}			120		
Reverse Transfer Capacitance	C _{rss}			90		
Total Gate Charge	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 8.4 A		13		nC
Gate-Source Charge	Q _{gs}			2.3		
Gate-Drain Charge	Q _{gd}			3.2		
Gate Resistance	R _g	f = 1 MHz		8.0		Ω
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = - 30 V, R _L = 3.57 Ω I _D ≅ - 8.4 A, V _{GEN} = - 10 V, R _G = 2.5 Ω		5	10	ns
Rise Time ^c	t _r			14	25	
Turn-Off Delay Time ^c	t _{d(off)}			15	25	
Fall Time ^c	t _f			7	12	
Source-Drain Diode Ratings and Characteristics (T _C = 25 °C) ^b						
Pulsed Current	I _{SM}			- 20		A
Forward Voltage ^b	V _{SD}	I _F = - 2 A, V _{GS} = 0 V		- 0.9	- 1.3	V
Reverse Recovery Time	t _{rr}	I _F = - 8 A, di/dt = 100 A/μs		50	80	ns
Reverse Recovery Time	Q _{rr}			80	120	nC

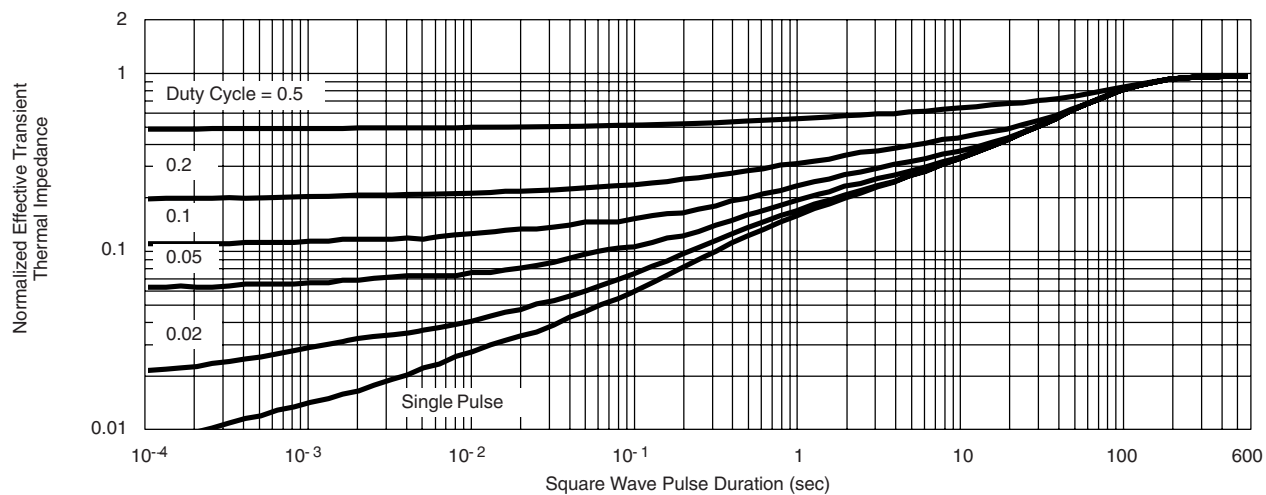
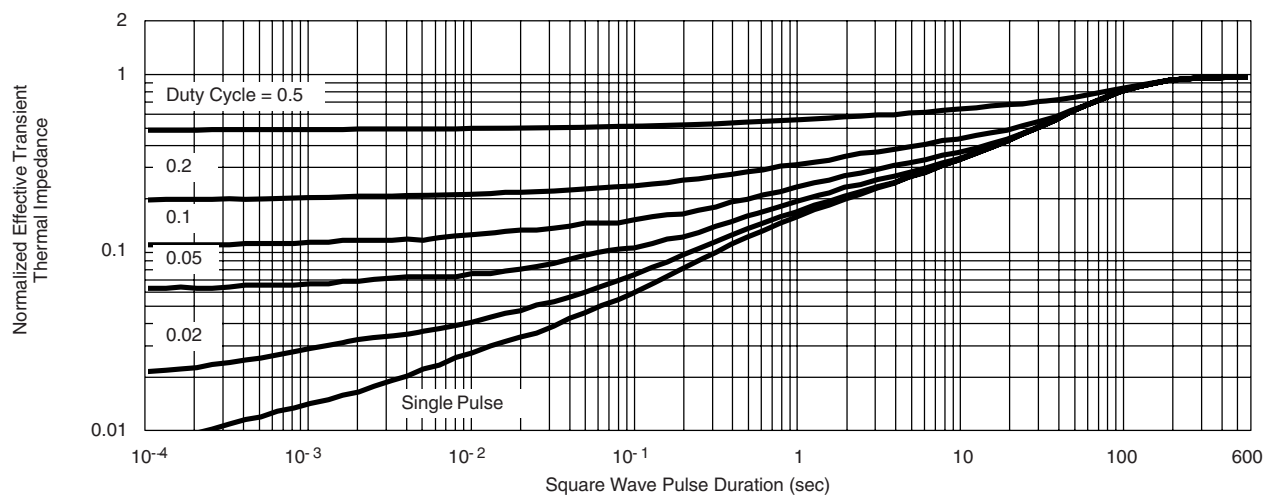
Notes:

- a. Guaranteed by design, not subject to production testing.
 b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 c. Independent of operating temperature.

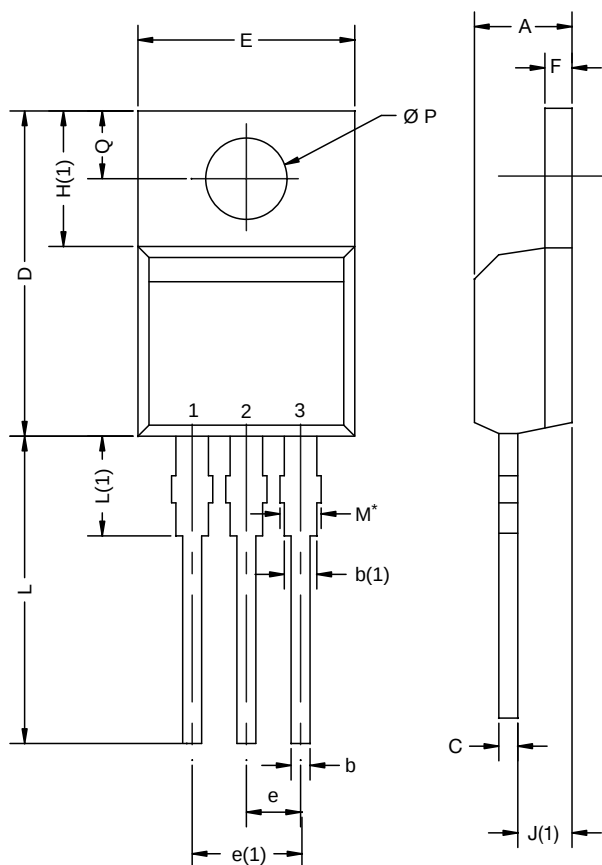
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

Gate Charge

TYPICAL CHARACTERISTICS 25 °C unless noted

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage
THERMAL RATINGS

Drain Current vs. Case Temperature

Safe Operating Area

THERMAL RATINGS**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118

ECN: X12-0208-Rev. N, 08-Oct-12
DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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